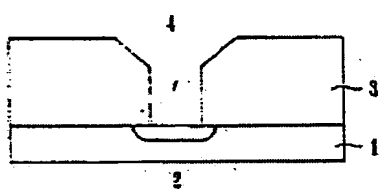


**ABSTRACT OF Korean Patent Application No. 10-1995-0017296**

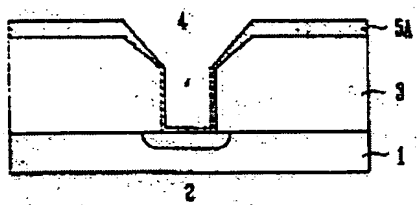
There is provided a method for forming a diffusion layer of a semiconductor device. In accordance with the present invention, a thick diffusion preventing layer having double  
5 structure is formed in a contact hole. A method for forming a diffusion preventing layer is performed through two stages so as to form a single-layered diffusion preventing layer having the same thickness as a conventional diffusion layer in the outside of the contact hole. In accordance with the present invention, silicon ion and aluminum ion in a contact unit are prevented from being diffused with each other, and it is possible to suppress  
10 increasing ratio of step difference. Thus, a metal interconnection process is easily performed, and reliability of devices can be increased.



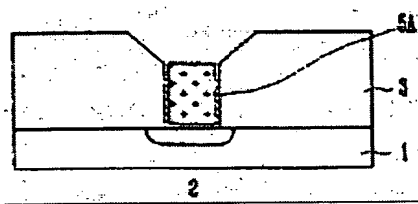
도면1a



도면1b



도면1c



도면1d

